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October 2016

# FPF2895 28 V / 5 A Rated Current Limit Switch with OVP and TRCB

#### **Features**

- 28 V / 5 A Capability
- Wide Input Voltage Range: 4 V ~ 22 V
- Ultra Low On-Resistance
  - Typ. 27 m $\Omega$  at 5 V and 25 °C
- Adjustable Current Limit with external RSET
  - 500 mA ~ 5 A
- Selectable OVLO with OV1 and OV2 Logic Input
  - $-5.95 V \pm 50 mV$
  - $-10 V \pm 100 mV$
  - $-14 V \pm 280 mV$
  - $-23 V \pm 460 mV$
- Selectable ON Polarity
- Selectable Over-Current Behavior
  - Auto-Restart Mode
  - Current Source Mode
- True Reverse Current Block
- Thermal Shutdown
- Open Drain Fault FLAGB Output
- UL60950-1 & IEC 60950-1 Certification 5 A Max Loading
- Robust ESD Capability
  - 2 kV HBM & 1 kV CDM
  - 15 kV Air Discharge & 8 kV Contact Discharge under IEC 61000-4-2

## **Description**

The FPF2895 features a 28 V and 5 A rated current limit power switch, which offers Over-Current Protection (OCP), Over-Voltage Protection (OVP), and True Reverse Current Block (TRCB) to protect system. It has low On-resistance of typical 27 m $\Omega$  with WL-CSP can operate over an input voltage range of 4 V to 22 V.

The FPF2895 supports ±10% of current limit accuracy, over-current range of 500 mA to 5 A, flexible operations such as selectable OVP, selectable ON polarity and selectable OCP behavior, which can be optimized according to system requirements.

The FPF2895 is available in a 24-bump, 1.67 mm  $\times$  2.60 mm Wafer-Level Chip-Scale Package (WL-CSP) with 0.4 mm pitch.

## **Applications**

- Laptop, Desktop Computing and Monitor
- Power Accessories

#### **Related Resources**

www.fairchildsemi.com

## Ordering Information

Part Number	Operating Temperature Range	Top Mark	Package	Packing Method
FPF2895UCX	-40°C – +85°C	Т9	24-Ball, 0.4 mm Pitch WLCSP	Tape & Reel

## **Application Diagram**

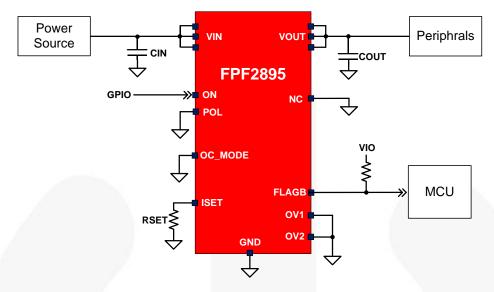


Figure 1. Typical Application

## **Block Diagram**

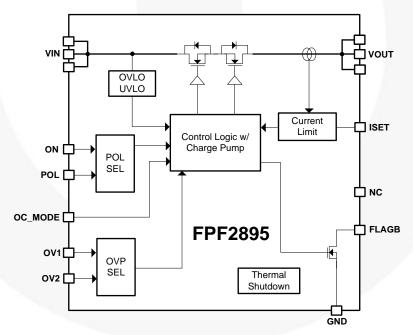
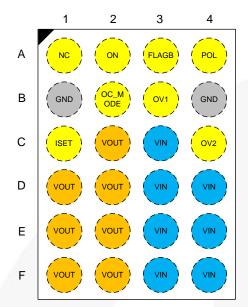
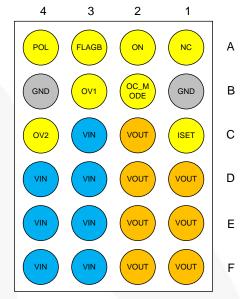


Figure 2. Functional Block Diagram

## **Pin Configuration**





Pin Configuration (Top View)

Pin Configuration (Bottom View)

Figure 3. 24 Ball WL\_CSP, 4 x 6 Array, 0.4 mm Pitch, 250 µm Ball

## **Pin Definitions**

Name	Bump	Туре	Description	
VIN	C3, D3, D4, E3, E4, F3, F4	Input/Supply	Switch Input and Device Supply	
VOUT	C2, D1, D2, E1, E2, F1, F2	Output	Switch Output to Load	
NC	A1	Dummy	Recommended to connect to GND	
ON	A2	Input	Internal pull-down resistor of 5 M $\Omega$ is included. Active polarity is depending on POL state. (1)	
POL	A4	Input	Enable Polarity Selection. Internal pull-up of 5 M $\Omega$ is included. HIGH (or Floating): Active LOW LOW: Active HIGH <sup>(1)</sup>	
FLAGB	А3	Output	Active LOW, open drain output indicates an over-current, under-voltage, over-voltage, or over-temperature state.	
ISET	C1	Input	A resistor from ISET to ground set the current limit for the switch. See below selection table 1.	
OC_MODE	B2	Input	OCP behavior can be selected. Internal pull-up of 5 M $\Omega$ is included. HIGH (or Floating): Auto-restart mode during over-current condition. LOW: Current source mode during over-current condition. (1)	
OV1	В3	Input	Over-Voltage Selection Input 1. Internal pull-up of 5 M $\Omega$ is included and see below selection table 2. <sup>(1)</sup>	
OV2	C4	Input	Over-Voltage Selection Input 2. Internal pull-up of 5 M $\Omega$ is included and see Table 2. (1)	
GND	B1, B4	GND	Device Ground	

#### Note:

1. To avoid external noise influence when floating, recommend to connect these pins to a certain level.

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters			Max.	Unit
VIN, VOUT	VIN, VOUT to GND		-0.3	28.0	V
$V_{PIN}$	ON, POL, OC_MODE, ISET, FLAC	BB and OVn to GND	-0.3	6.0	V
I <sub>SW</sub>	Continuous Switch Current			5.5	Α
t <sub>PD</sub>	Total Power Dissipation at T <sub>A</sub> =25°0	C		2.08	W
T <sub>STG</sub>	Storage Junction Temperature			+150	°C
TJ	Operating Junction Temperature			+150	°C
$T_L$	Lead Temperature (Soldering, 10 Seconds)			+260	°C
ΘJA	Thermal Resistance, Junction-to-Ambient (1in. <sup>2</sup> pad of 2 oz. copper)			60 <sup>(2)</sup>	°C/W
	Electrostatic Discharge Capability	Human Body Model, ANSI/ESDA/JEDEC JS-001	2		
ESD	// •	Charged Device Model, JESD22-C101	1		kV
	IFC64000 4 2 System Level	Air Discharge	15		
	IEC61000-4-2 System Level	Contact Discharge	8		

#### Note:

2. Measured using 2S2P JEDEC std. PCB.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. ON does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
V <sub>IN</sub>	Supply Voltage	4.0	22.0	V
C <sub>IN</sub> / C <sub>OUT</sub>	Input and Output Capacitance	1.0		μF
T <sub>A</sub>	Ambient Operating Temperature	-40	+85	°C

## **Electrical Characteristics**

Unless otherwise noted, V<sub>IN</sub>=4 to 22 V, T<sub>A</sub>=-40 to 85°C; typical values are at V<sub>IN</sub>=5 V, C<sub>IN</sub>=C<sub>OUT</sub>=1  $\mu$ F, ON=HIGH, POL=OV1=OV2=OC\_MODE=GND and T<sub>A</sub> = 25°C.

Symbol	Parameter	Conditions		Min.	Тур.	Max.	Unit
Basic Ope	eration	•					
$V_{IN}$	Input Voltage			4		22	V
I <sub>SD_IN</sub>	V <sub>IN</sub> Shutdown Current	V <sub>ON</sub> =OFF, V <sub>IN</sub> =5.5 V, V <sub>OUT</sub> =SI	hort to GND		75	100	μA
			V <sub>IN</sub> =5 V		270	330	
ΙQ	Quiescent Current	I <sub>OUT</sub> =0 mA, V <sub>ON</sub> =ON	V <sub>IN</sub> =12 V		300	400	μΑ
			V <sub>IN</sub> =20 V		350	450	
			V <sub>IN</sub> =5 V		27	39	
$R_{ON}$	On Resistance	T <sub>A</sub> =25°C, I <sub>OUT</sub> =1 A	V <sub>IN</sub> =12 V		27	39	mΩ
			V <sub>IN</sub> =20 V		27	39	
I <sub>ON</sub>	ON Input Leakage	V <sub>ON</sub> =V <sub>IN</sub> or GND				2	μΑ
$V_{IH}$	ON Input Logic High Voltage	V <sub>IN</sub> =3 V~23 V		1.2			V
$V_{IL}$	ON Input Logic Low Voltage	V <sub>IN</sub> =3 V~23 V				0.4	V
	FLAGB Output Logic Low Voltage	V <sub>IN</sub> =5 V, I <sub>SINK</sub> =5 mA			0.1	0.2	V
I <sub>LKG</sub>	FLAGB Output High, Leakage Current	V <sub>IN</sub> =5 V, Switch ON				1	μA
Protection	าร						
I <sub>LIM</sub>	Current Limit <sup>(3)</sup>	$V_{IN}$ =5 V, $V_{OUT}$ =4 V, $R_{SET}$ =2.96 $T_A$ = -40 to 85°C	S kΩ,	1.35	1.50	1.65	A
ILIM		$V_{\text{IN}}$ =5 V, $V_{\text{OUT}}$ =4 V, $R_{\text{SET}}$ =1.48 k $\Omega$ , $T_{\text{A}}$ = -40 to 85°C		2.7	3.0	3.3	
$V_{FOLD}$	ILIM Foldback Trip Voltage <sup>(3)</sup>	V <sub>OUT</sub> under ILIM Mode			2		V
I <sub>FOLD</sub>	ILIM Foldback Gain <sup>(3)</sup>	V <sub>IN</sub> =5 V, V <sub>OUT</sub> < V <sub>FOLD</sub> , T <sub>A</sub> =25°C, OC_MODE=HIGH			500		mA
		V <sub>IN</sub> =5 V, V <sub>OUT</sub> < V <sub>FOLD</sub> , T <sub>A</sub> =25°C, OC_MODE=LOW			250		mA
	Under-Voltage Lockout	V <sub>IN</sub> Increasing			2.70	2.95	V
$V_{\text{UVLO}}$		V <sub>IN</sub> Decreasing		į.	2.5		
	UVLO Hysteresis				200		mV
		OV1=LOW, OV2=LOW	V <sub>IN</sub> Rising	22.54	23.00	23.46	_
			V <sub>IN</sub> Falling	22.34			_
		OV1=LOW, OV2=HIGH	V <sub>IN</sub> Rising	9.90	10.00	10.10	_
$V_{\text{OVLO}}$	Over-Voltage Lockout	·	V <sub>IN</sub> Falling	9.85			V
		OV1=HIGH, OV2=LOW	V <sub>IN</sub> Rising	13.72	14.00	14.28	
			V <sub>IN</sub> Falling	13.52		0.00	
		OV1=HIGH, OV2=HIGH	V <sub>IN</sub> Rising	5.90	5.95	6.00	
		D 400 0 0 0 5 V V	V <sub>IN</sub> Falling	5.85			
t <sub>OVP</sub>	OVP Response Time <sup>(3)</sup>	$R_L$ =100 $\Omega$ , $C_L$ =0 $\mu$ F, $V_{IN}$ > $V_{OVLO}$ to $V_{OUT}$ =0.9 $\times$ $V_{IN}$				150	ns
V <sub>T_RCB</sub>	TRCB Protection Trip Point	V <sub>OUT</sub> - V <sub>IN</sub>			25	40	mV
$V_{R\_RCB}$	TRCB Protection, Release Point	V <sub>IN</sub> - V <sub>OUT</sub>			25	40	mV
t <sub>RCB</sub>	TRCB Response Time <sup>(3)</sup>	V <sub>IN</sub> =5 V, V <sub>ON</sub> =HIGH/LOW			5		μs
t <sub>RCB_Release</sub>	TRCB Release Time <sup>(3)</sup>	V <sub>IN</sub> =5 V, Enabled			1		μs
t <sub>OC</sub>	Over Current Response	V <sub>IN</sub> =5 V, Moderate OC			20		μs
.00	Time <sup>(3)</sup>	V <sub>IN</sub> =5 V, Hard Short			5		μο

## **Electrical Characteristics**

Unless otherwise noted, V<sub>IN</sub>=4 to 22 V, T<sub>A</sub>=-40 to 85°C; typical values are at V<sub>IN</sub>=5 V, C<sub>IN</sub>=C<sub>OUT</sub>=1  $\mu$ F, ON=HIGH, POL=OV1=OV2=OC\_MODE=GND and T<sub>A</sub> = 25°C.

Symbol	Parameter	Conditions		Тур.	Max.	Unit
I <sub>SD_OUT</sub>	VOUT Shutdown Current	V <sub>ON</sub> =OFF, V <sub>OUT</sub> =5 V, V <sub>IN</sub> =Short to GND			2	μA
TSD	Thermal Shutdown <sup>(3)</sup>	Shutdown Threshold		150		°C
130	Thermal Shuldown	Hysteresis		20		
Dynamic	Behavior					
t <sub>DON</sub>	Delay On Time	$R_L$ =100 $\Omega$ , $C_L$ =1 $\mu F$		1		ms
t <sub>R</sub>	V <sub>OUT</sub> Rise Time	$R_L=100~\Omega,~C_L=1~\mu F$		1		ms
ton	Turn-On Time	$R_L$ =100 $\Omega$ , $C_L$ =1 $\mu F$		2		ms
t <sub>DOFF</sub>	Delay Off Time	$R_L=100 \Omega$ , $C_L=1 \mu F$		10		μs
t <sub>F</sub>	V <sub>OUT</sub> Fall Time	$R_L=100 \Omega$ , $C_L=1 \mu F$		200		μs
t <sub>OFF</sub>	Turn-Off Time	$R_L$ =100 Ω, $C_L$ =1 $\mu$ F		210		μs
t <sub>BLANK</sub>	Over-Current Blanking Time(3)	OC_MODE=HIGH		5		ms
t <sub>RSTRT</sub>	Auto-Restart Time <sup>(3)</sup>	OC_MODE=HIGH		200		ms
t <sub>QUAL</sub>	Over-Current Qualification Time <sup>(3)</sup>	OC_MODE=LOW		5		ms
	<i>f</i>	Restart-up during or after OC		3		
t <sub>DEB</sub>	FLAGB Debounce Time <sup>(3)</sup>	Restart-up during or after Thermal shutdown	Y	15		ms
		Restart-up during or after UVLO		1		

#### Note:

3. Guaranteed by characterization and design, not production test.

## **Setting Current Limit**

FPF2895 current limit is set with an external resistor connected between  $I_{\text{SET}}$  and GND. This resistor is selected using the following equation:

The resistor can be selected using 0. Resistor tolerance of 1% or less is recommended

 $R_{SET}[k\Omega] = 4448.6 / I_{LIM}[mA]$  (1)

Table 1. ILIM vs. RSET Look-up Table

RSET [kΩ]		ILIM [mA]	
NOET [K22]	Min.	Тур.	Max.
8.89	450	500	550
7.41	540	600	660
6.35	630	700	770
5.56	720	800	880
4.94	810	900	990
4.45	900	1000	1100
4.04	990	1100	1210
3.71	1080	1200	1320
3.42	1170	1300	1430
3.18	1260	1400	1540
2.96	1350	1500	1650
2.78	1440	1600	1760
2.62	1530	1700	1870
2.47	1620	1800	1980
2.34	1710	1900	2090
2.22	1800	2000	2200
2.12	1890	2100	2310
2.02	1980	2200	2420
1.93	2070	2300	2530
1.85	2160	2400	2640
1.78	2250	2500	2750
1.71	2340	2600	2860
1.65	2430	2700	2970
1.59	2520	2800	3080
1.53	2610	2900	3190
1.48	2700	3000	3300
1.43	2790	3100	3410
1.39	2880	3200	3520
1.35	2970	3300	3630
1.31	3060	3400	3740
1.27	3150	3500	3850
1.24	3240	3600	3960
1.20	3330	3700	4070
1.17	3420	3800	4180
1.14	3510	3900	4290
1.11	3600	4000	4400
1.08	3690	4100	4510
1.06	3780	4200	4620
1.03	3870	4300	4730
1.01	3960	4400	4840

Table 1. ILIM vs. RSET Look-up Table (Continued)

RSET [kΩ)	ILIM [mA]				
	Min.	Тур.	Max.		
0.99 <sup>(4)</sup>	4050	4500	4950		
0.97	4140	4600	5060		
0.95	4230	4700	5170		
0.93	4320	4800	5280		
0.91	4410	4900	5390		
0.89	4500	5000	5500		

#### Note:

Table 2. OVLO Level Selection

OV1	OV2	OVLO
LOW	LOW	23 V ±460 mV
LOW	HIGH (Floating)	10 V ±100 mV
HIGH (Floating)	LOW	14 V ±280 mV
HIGH (Floating)	HIGH (Floating)	5.95 V ±50 mV

Table 3. Device Enable Polarity Selection

POL	ON	Device State	ON Polarity
LOW	LOW (Floating)	OFF	Active LICH
LOW	HIGH	ON	Active HIGH
HIGH (Floating)	LOW (Floating)	ON	Active LOW
HIGH (Floating)	HIGH	OFF	Active LOW

<sup>4.</sup> Passed UL&CB certification with max. 5 A output current.

## **Timing Diagrams**

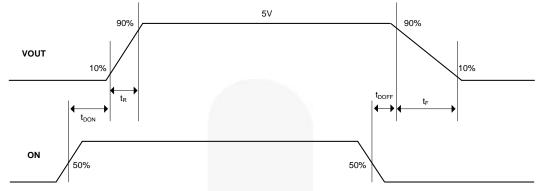


Figure 4. Normal ON/OFF Operation by ON (POL=GND)

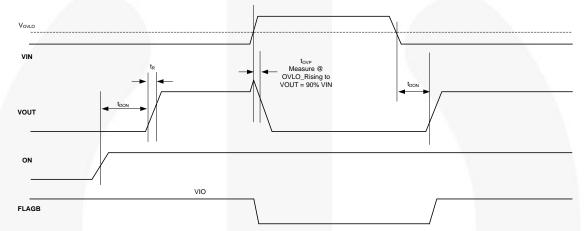


Figure 5. OVLO Operation (POL=GND & FLAGB is pulled up with an external VIO)

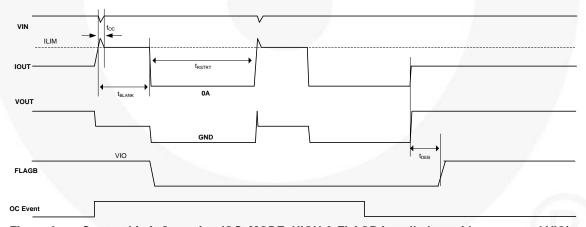


Figure 6. Current Limit Operation (OC\_MODE=HIGH & FLAGB is pulled up with an external VIO)

## Timing Diagrams (Continued)

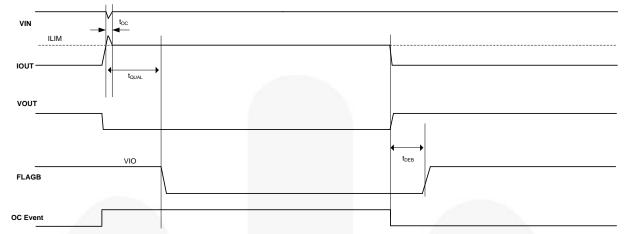


Figure 7. Current Limit Operation (OC\_MODE=LOW & FLAGB is pulled up with an external VIO)

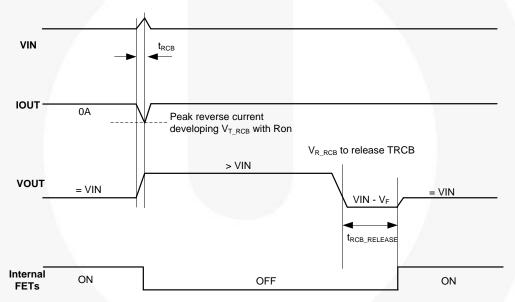
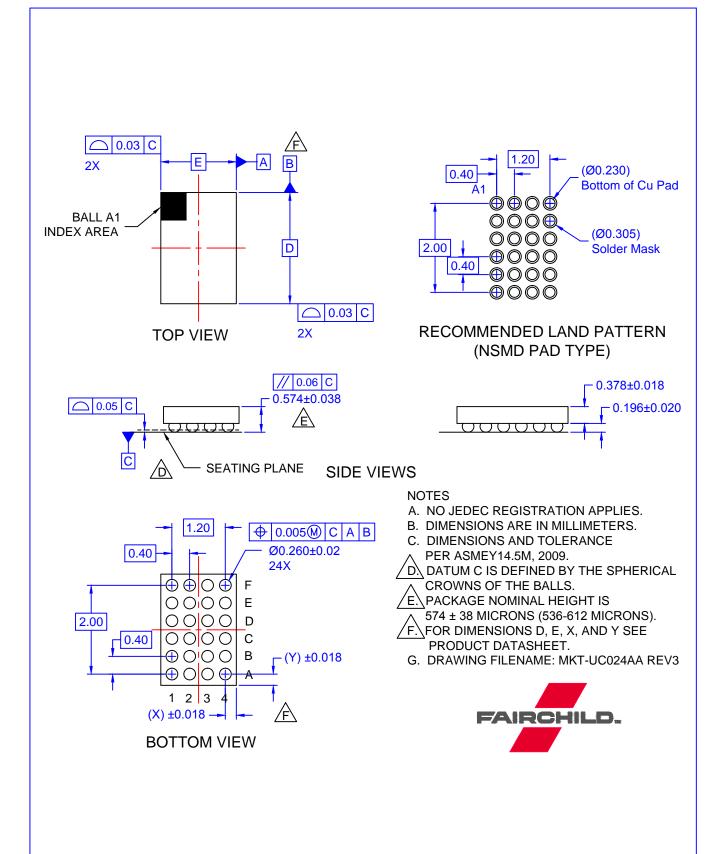


Figure 8. TRCB Operation (Device is Enabled)

The table below pertains to the Marketing outline drawing on the following page.

## **Product-Specific Dimensions**

D	E	X	Y
2600 μm ±30 μm	1670 μm ±30 μm	235 μm ±18 μm	300 μm ±18 μm



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